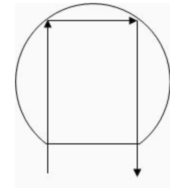
Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none / semi std	wafer vendor
	5.0	Overall Thickness	525.00 +/- 25.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<10.00um	ADE, 100% measurement
	7.0	Bow	<40.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<40.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	FZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	13.0	Handle Thickness	525.00 +/- 25.00 µm	ADE, 100%
	14.0	Handle Doping Type	N	Wafer Vendor
	15.0	Handle Dopant	Phosphorous	Wafer Vendor
	16.0	Handle Resistivity	> 1000 Ohmcm	Wafer Vendor
	17.0	Backside Finish	Polished with 3.6um +/- 0.6um oxide and lasermark,. No polysilicon. Planarise after phosphorous deposition of poly	Guaranteed by process
	17.1	Backside Lasermark	On wafer BACKSIDE for identification. Scribe format: YYMM-XXXX (unique scribe)	
DeviceSilicon	18.0	LPD Count	<30.00pces	@0.3um, Tencor 6220 particle counter
	19.0	Scratches	0	Bright Light, 100% (note 2)
	20.0	Haze	none	Bright Light, 100% (note 2)
	21.0	Surface	front side prime polished (before oxide and poly deposition)	Guaranteed by process
	23.0	Device Field Oxidation	40,000.00 +/- 2,000.00 A	Nanospec 4%, 5pt
Trench	24.0	Poly refill thickness	20000A +/- 1000A, doped as per the schedule in notes. Sheet resistance of poly <2.8 Ohms per sq	4 pt probe 100%

Part Number	Customer		
Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

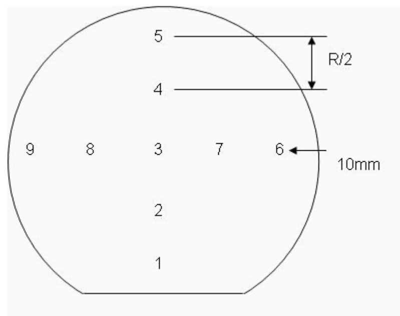
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information